



UF130N07

Preliminary

Power MOSFET

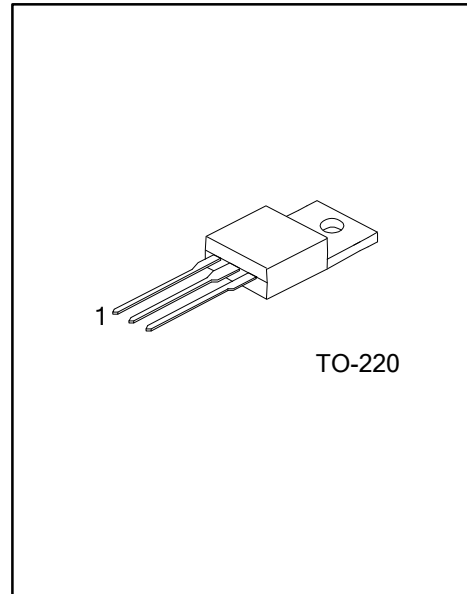
130A, 70V N-CHANNEL POWER MOSFET

DESCRIPTION

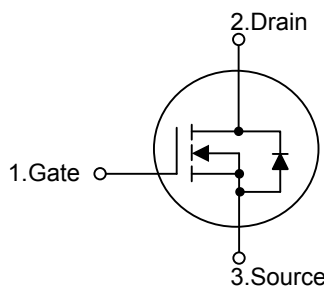
The UTC **UF130N07** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * Fast switching speed
- * $R_{DS(ON)} < 9.0m\Omega @ V_{GS}=10V, I_D=65A$
- * 100% avalanche tested
- * Improved dv/dt capability



SYMBOL



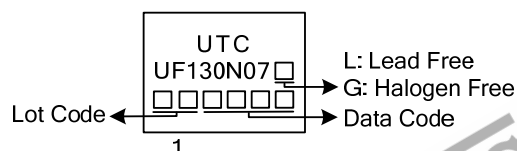
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF130N07L-TA3-T	UF130N07G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UF130N07L-TA3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TA3: TO-220
	(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	70	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	Continuous	I_D	130	A
	Pulsed	I_{DM}	520	A
Avalanche Current (Note 2)		I_{AR}	130	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	845	mJ
Peak Diode Recovery dv/dt		dv/dt	3.6	V/ns
Power Dissipation		P_D	175	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 130\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.714	$^\circ\text{C}/\text{W}$

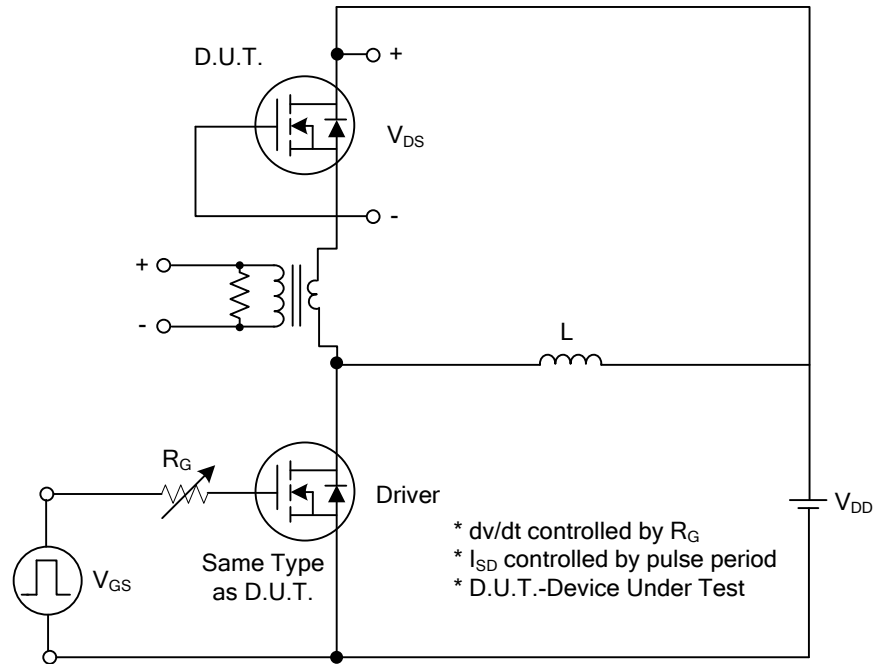
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	70			V			
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=70\text{V}$, $V_{GS}=0\text{V}$			10	μA			
Gate- Source Leakage Current		I_{GSS}							
							Forward	$V_{DS}=0\text{V}$, $V_{GS}=+20\text{V}$	+100
						Reverse	$V_{DS}=0\text{V}$, $V_{GS}=-20\text{V}$	-100	nA
ON CHARACTERISTICS									
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V			
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=65\text{A}$			9	m Ω			
DYNAMIC PARAMETERS									
Input Capacitance	C_{ISS}	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$		5100		pF			
Output Capacitance	C_{OSS}			1100		pF			
Reverse Transfer Capacitance	C_{RSS}			81		pF			
SWITCHING PARAMETERS									
Total Gate Charge	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$, $I_G=100\mu\text{A}$ (Note 1, 2)		450		nC			
Gate to Source Charge	Q_{GS}			22		nC			
Gate to Drain Charge	Q_{GD}			52		nC			
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G = 25\Omega$ (Note 1, 2)		120		ns			
Rise Time	t_R			250		ns			
Turn-OFF Delay Time	$t_{D(OFF)}$			1500		ns			
Fall-Time	t_F			600		ns			
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Maximum Body-Diode Continuous Current	I_S				130	A			
Maximum Body-Diode Pulsed Current	I_{SM}				520	A			
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=130\text{A}$			1.4	V			
Reverse Recovery Time	t_{RR}	$V_{GS}=0\text{V}$, $I_S=30\text{A}$,		82		ns			
Reverse Recovery Charge	Q_{RR}	$di/dt=100\text{A}/\mu\text{s}$		230		nC			

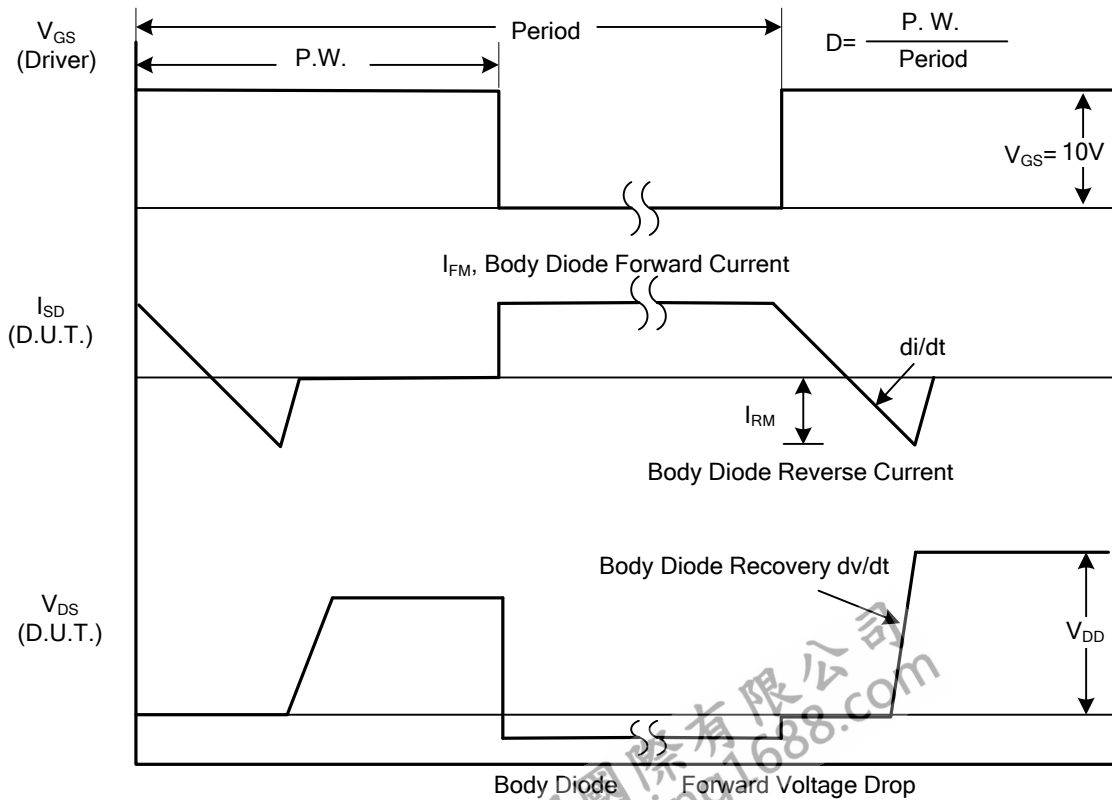
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

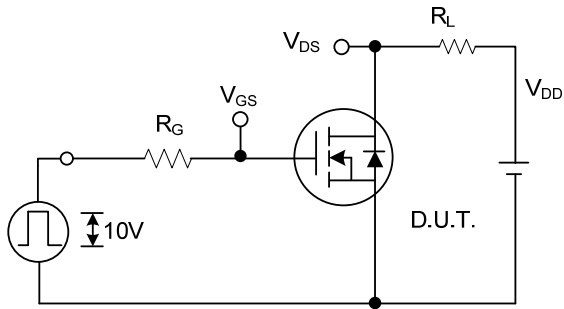


Peak Diode Recovery dv/dt Test Circuit

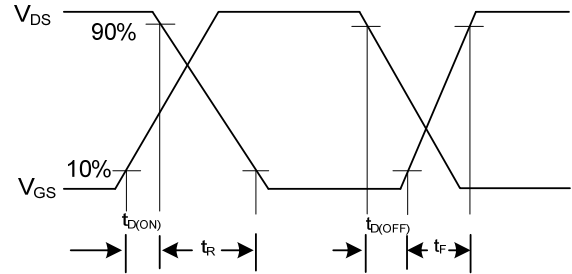


Peak Diode Recovery dv/dt Waveforms

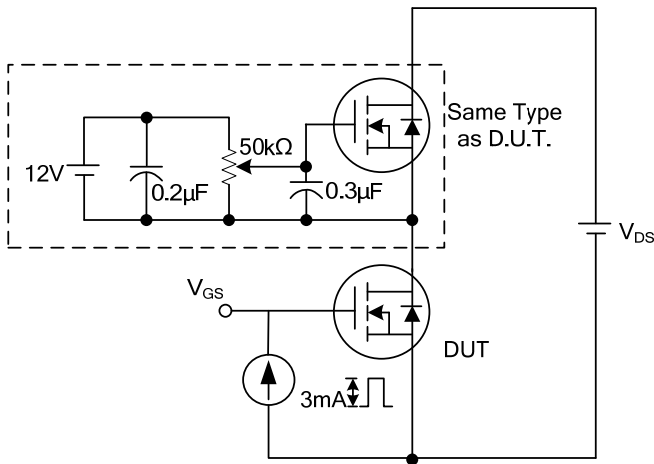
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



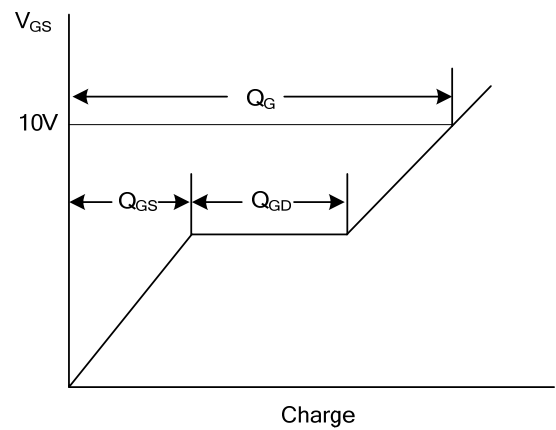
Switching Test Circuit



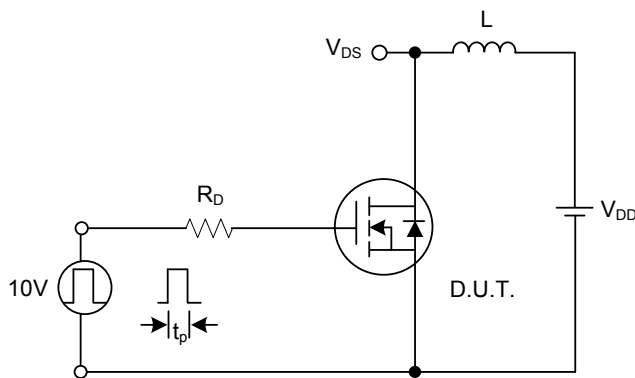
Switching Waveforms



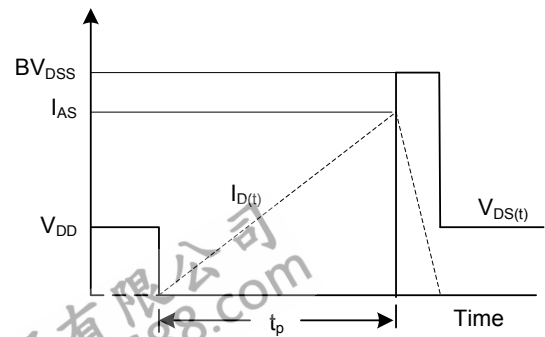
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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